



SEMICONDUCTOR

SS8550LT1

Shandong Yiguang Electronic Joint stock Co., Ltd

TECHNICAL DATA

PNP EPITAXIAL SILICON TRANSISTOR

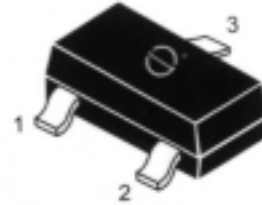
2W OUTPUT AMPLIFIER OF PORTABLE**RADIOS IN CLASS****B PUSH-PULL OPERATION**

- * Complement to SS8050LT1
- * Collector Current :Ic= -800mA
- * High Total Power Dissipation :Pc=625mW

ABSOLUTE MAXIMUM RATINGS at Ta=25

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	-40	V
Collector-Emitter Voltage	Vceo	-25	V
Emitter-Base Voltage	Veb	-6	V
Collector Current	Ic	-800	mA
Collector Dissipation Ta=25 *	P _D	625	mW
Junction Temperature	T _j	150	
Storage Temperature	T _{stg}	-55-150	

Package:SOT-23



PIN:	1	2	3
STYLE			
NO.1	B	E	C

ELECTRICAL CHARACTERISTICS at Ta=25

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	-40			V	Ic=-100uA Ie=0
Collector-Emitter Breakdown Voltage#	BVceo	-25			V	Ic= -1mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	-6			V	Ie= -100uA Ic=0
Collector Cutoff Current	Icbo			-100	NA	Vcb= -40V Ie=0
Emitter Cutoff Current	Iceo			-100	NA	Vce=-20 V Ie=0
Emitter Cutoff Current	Iebo			-100	Na	Veb=-5V Ic=0
DC Current Gain	Hfe ₁	120		350		Vce= -1V Ic= 100mA
DC Current Gain	Hfe ₂	40				Vce= -1V Ic= 800mA
Collector-Emitter Saturation Voltage	Vce(sat)			-0.6	V	Ic= -800mA Ib= -80mA
Base-Emitter Saturation Voltage	Vbe(sat)			-1.2	V	Ic= -800mA Ib= -80mA
Current Gain-Bandwidth Product	f _T	100			MHz	Vce=-10V Ic=-50mA f=30MHz

* Total Device Dissipation : FR=1x0.75x0.062in Board,Derate 25 .

Pulse Test : Pulse Width 300uS,Duty cycle 2%

CLASSIFICATION OF Hfe₍₁₎

Rank	L	H
Range	120—200	200—350

DEVICE MARKING:

SS8550LT1=Y2



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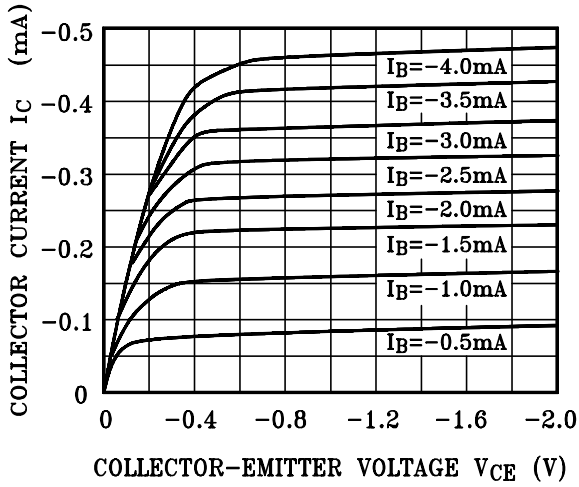
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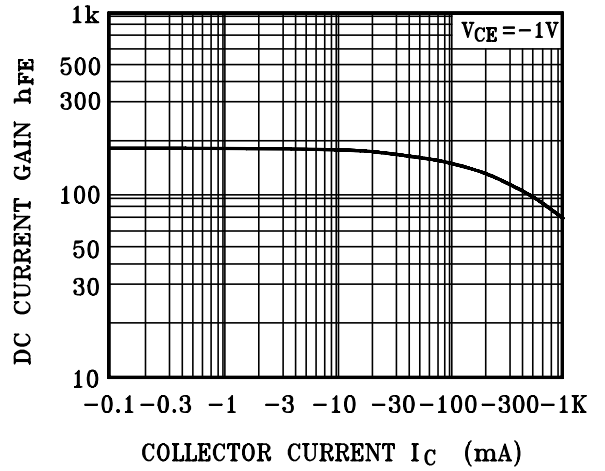
PNPEPITAXIAL SILICON TRANSISTOR

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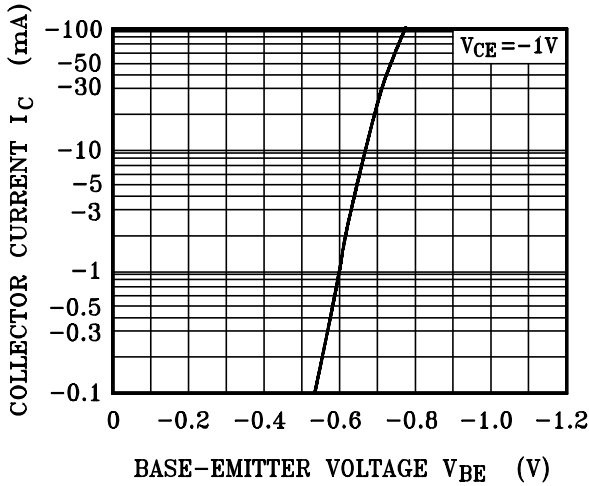
$I_C - V_{CE}$



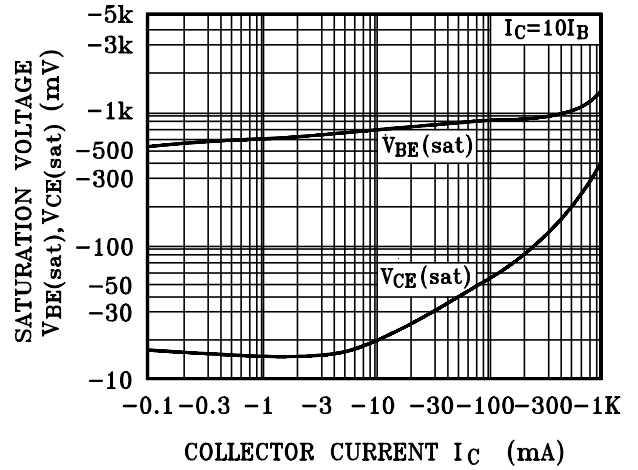
$h_{FE} - I_C$



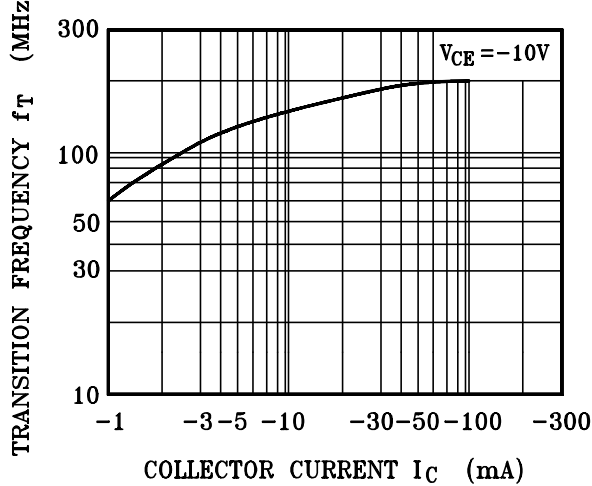
$I_C - V_{BE}$



$V_{BE(sat)}, V_{CE(sat)} - I_C$



$f_T - I_C$



$C_{ob} - V_{CB}$

